

**ZVN4310G** 

#### 100V N-CHANNEL ENHANCEMENT MODE VERTICAL MOSFET IN SOT223

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
-60V	125mΩ @ V <sub>GS</sub> = -10V	-4.3A
	190mΩ @ V <sub>GS</sub> = -4.5V	-3.5A

## **Features and Benefits**

- V<sub>(BR)DSS</sub> > 100V
- $R_{DS(on)} \le 0.54\Omega @ V_{GS} = 10V$
- Maximum Continuous Drain Current I<sub>D</sub> = 1.67A
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part.
   A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.
   <a href="https://www.diodes.com/quality/product-definitions/">https://www.diodes.com/quality/product-definitions/</a>
- An Automotive-Compliant Part is Available Under Separate Datasheet (ZXMP6A17GQ)

### **Description and Applications**

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for highefficiency power management applications.

- DC-DC converters
- Solenoids/relay driver for automotive applications

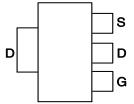
### **Mechanical Data**

- Package: SOT223 (Type DN)
- Package Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

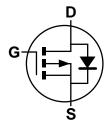
SOT223 (Type DN)



Top View



Pin Out - Top View



**Equivalent Circuit** 

## Ordering Information (Note 4)

Part Number	Pookage	Packing		
	Package	Qty.	Carrier	
ZVN4310GTA	SOT223 (Type DN)	1,000	Tape & Reel	

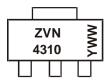
Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

January 2022



## **Marking Information**



ZVN4310 = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 1= 2021) WW or  $\overline{W}W = \text{Week Code } (01~53)$ 

## Maximum Ratings (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	100	V
Gate-Source Voltage	$V_{GSS}$	±20	V
Continuous Drain Current	I <sub>D</sub>	1.67	А
Pulsed Drain Current (Note 6)	I <sub>DM</sub>	12	A

## Thermal Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	$P_{D}$	3	W
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	41.7	°C/W
Thermal Resistance, Junction to Leads	(Note 7)	$R_{ heta JL}$	8.84	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# **Electrical Characteristics** (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	-	-	V	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	-	-	10 100	μA μA	$V_{DS} = 100V, V_{GS} = 0V$ $V_{DS} = 80V, V_{GS} = 0V, T_A = +125$ °C	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±20	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$	
On-State Drain Current	I <sub>D(on)</sub>	9	-	-	Α	$V_{GS} = 10V, V_{DS} = 10V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	$V_{GS(th)}$	1	-	3	V	$V_{DS} = V_{GS}$ , $I_D = 1mA$	
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	-	0.4 0.5	0.54 0.75	Ω	$V_{GS} = 10V, I_D = 3.3A$ $V_{GS} = 5V, I_D = 1.5A$	
Forward Transconductance	g <sub>fs</sub>	0.6	-	-	S	$V_{DS} = 10V, I_D = 3.3A$	
DYNAMIC CHARACTERISTICS (Note 8)	0.0						
Input Capacitance	C <sub>iss</sub>	-	-	350	pF	.,	
Output Capacitance	Coss	-	-	140	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, -f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	-	20	pF	T = 1.0MHZ	
Turn-On Delay Time	t <sub>D(on)</sub>	-	-	8	ns	$V_{DD} = 25V$ , $I_{D} = 3A$ , $V_{GEN} = 10V$ , $R_{GS} = 50\Omega$	
Turn-On Rise Time	t <sub>R</sub>	-	-	25	ns		
Turn-Off Delay Time	t <sub>D(off)</sub>	-	-	30	ns		
Turn-Off Fall Time	t <sub>F</sub>	-	-	16	ns		

5. For a device mounted on 50mm X 50mm X 1.6mm FR-4 PCB with high coverage of single sided 2oz copper, in still air condition.

6. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.

7. Thermal resistance from junction to solder-point (at the end of the drain lead).

8. Short duration pulse test used to minimize self-heating effect.



### **Electrical Characteristics**

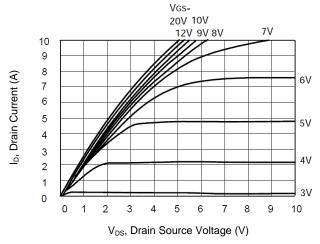


Figure 1. Saturation Characteristics

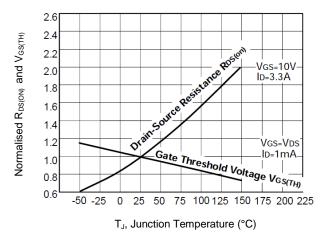


Figure 3. Normalised  $R_{\text{DS}(\text{ON})}$  and  $V_{\text{GS}(\text{TH})}$  vs. Temperature

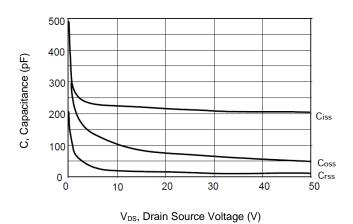


Figure 5. Capacitance vs. Drain-source Voltage

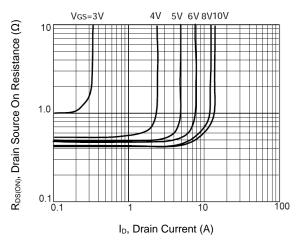


Figure 2. On-resistance vs. Drain Current

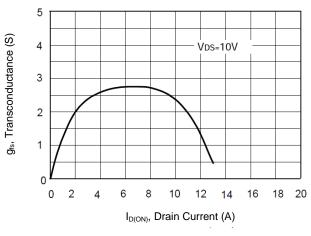


Figure 4. Transconductance vs. Drain Current

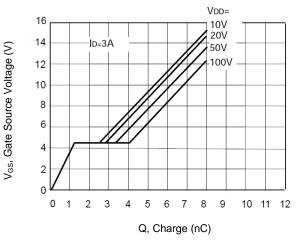


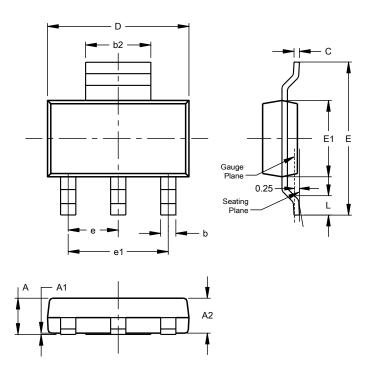
Figure 6. Gate Charge vs. Gate-source Voltage



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT223 (Type DN)

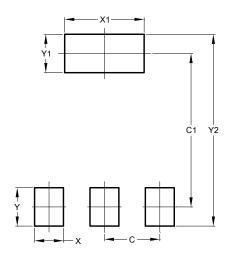


SOT223 (Type DN)				
Dim	Min	Max	Тур	
Α		1.70		
A1	0.01	0.15		
A2	1.50	1.68	1.60	
b	0.60	0.80	0.70	
b2	2.90	3.10		
С	0.20	0.32		
D	6.30	6.70		
E	6.70	7.30		
E1	3.30	3.70		
е			2.30	
e1			4.60	
L	0.85			
All Dimensions in mm				

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT223 (Type DN)



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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